Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- · Sensitive gate
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- · General purpose phase control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	16	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	155	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	-	170	A
Tj	junction temperature		-	-	125	°C
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	10	mA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$		-	11	25	mA	
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	4	30	mA	
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; <u>Fig. 10</u>		-	1.2	1.6	V	
Dynamic chara	Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		-	50	-	V/µs	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		Ν
2	T2	main terminal 2		T2 — T1 G sym051
3	G	gate		J
mb	T2	mounting base; main terminal 2	N P	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT139B-600E	TO263	BT139B-600E,118	Reel	800	TO263N (N)	26-Sep-2016
					TO263P (P)	12-Jun-2023

7. Marking

Table 4. Marking codes

Type number	Marking codes			
	Assembly factory: N	Assembly factory: P		
BT139B-600E	BT139B 600E PJNxxxx xx	BT139B 600E PJPxxxx xx		

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	16	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	155	Α
	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	170	Α	
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	120	A²s

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Symbol	Parameter	Conditions	Min	Max	Unit
dl _T /dt	rate of rise of on-state current	I _G = 50 mA	-	50	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

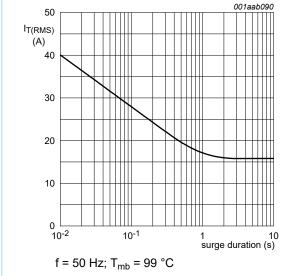


Fig. 1. RMS on-state current as a function of surge duration; maximum values

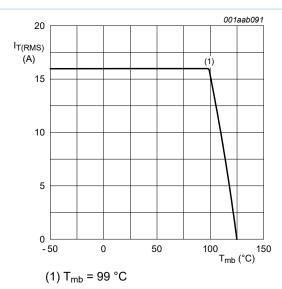
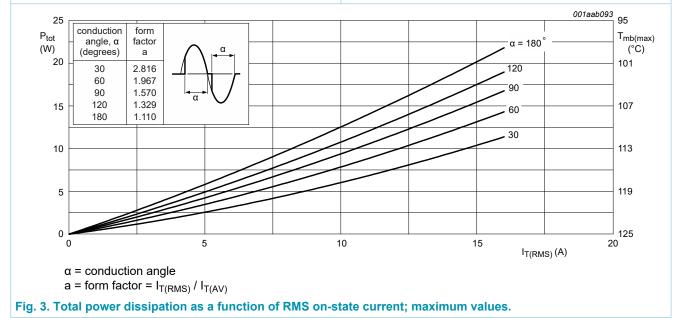


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



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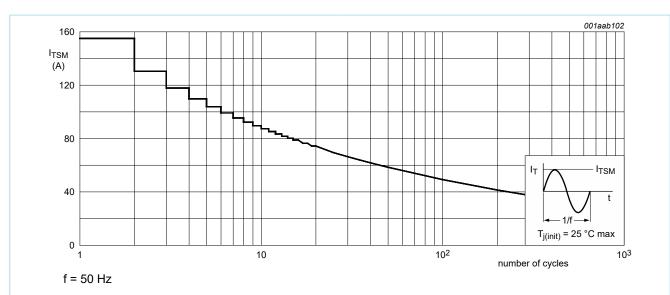


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

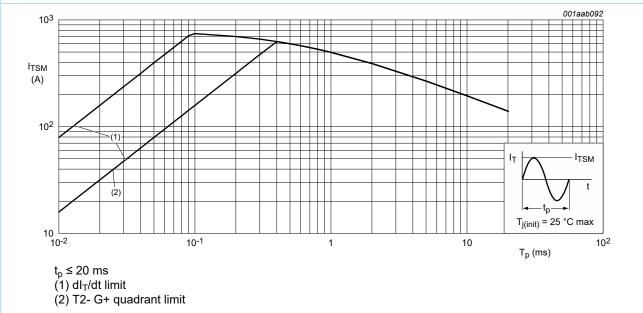


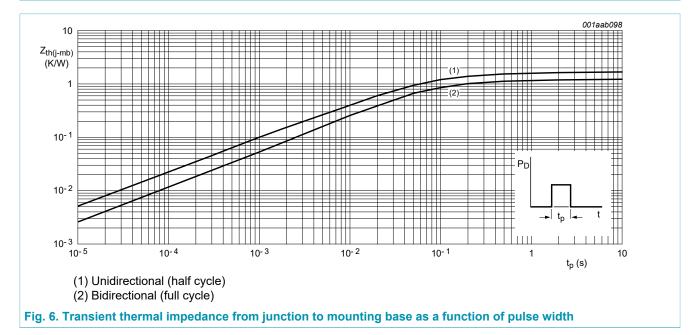
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance from junction to mounting base		half cycle; Fig. 6	-	-	1.7	K/W
	full cycle; Fig. 6	-	-	1.2	K/W	
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	minimum footprint; FR4 board	-	55	-	K/W



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	4	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
I _L latching currer	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	3.2	30	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{}$	-	16	40	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{}$	-	4	30	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2- G+;$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{}$	-	5.5	40	mA
l _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	4	30	mA
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics		'			,
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs

3

2

1

0

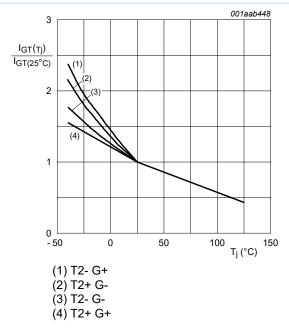
-50

 I_{L}

I_{L(25°C)}

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001aab100



100 _{Tj} (°C) 150 Fig. 8. Normalized latching current as a function of junction temperature

50

0



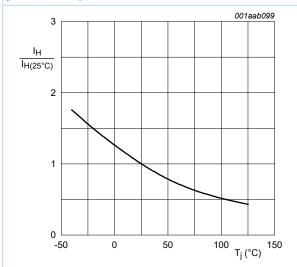
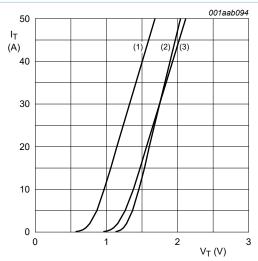


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.195 V; R_s = 0.018 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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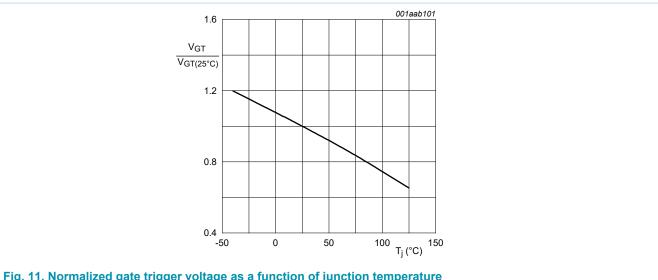
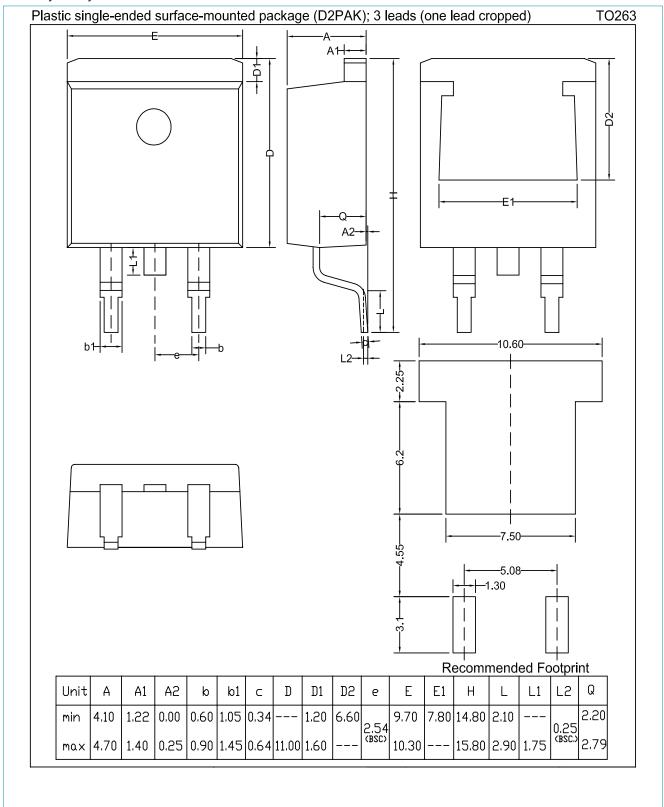


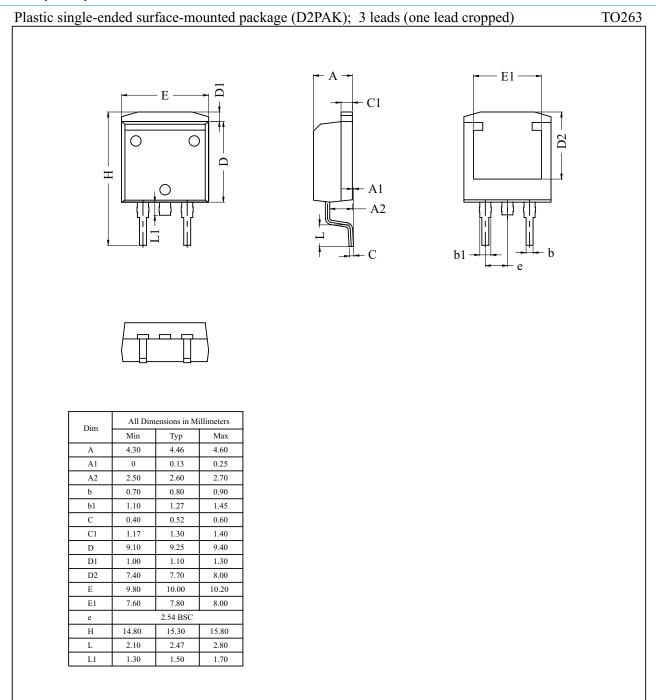
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Assembly factory: N



Assembly factory: P



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com
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Date of release: 03 January 2024

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